

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|---|------------------|
| 2 | 1136 | 430/30.ccls. | USPAT | 2004/09/08 15:49 |
| 5 | 706 | ((356/\$).CCLS.) and ((index near4 refract\$3) or (refract\$3 adj index))) and (grating and (wafer or semiconductor))) | USPAT | 2004/09/08 15:50 |
| 6 | 486 | ((356/\$).CCLS.) and ((index near4 refract\$3) or (refract\$3 adj index))) and (grating and (wafer or semiconductor))) and (liquid or medium or solution or bath) | USPAT | 2004/09/08 15:51 |
| 7 | 4 | ((356/\$).CCLS.) and ((index near4 refract\$3) or (refract\$3 adj index))) and (grating and (wafer or semiconductor))) and (liquid or medium or solution or bath)) and (immersion with (lithography or medium)) | USPAT | 2004/09/08 15:58 |
| 8 | 92 | ((356/\$).CCLS.) and ((index near4 refract\$3) or (refract\$3 adj index))) and (grating and (wafer or semiconductor))) and (liquid or medium or solution or bath)) and lithography | USPAT | 2004/09/08 15:59 |
| 9 | 988 | 438/5.ccls. or 438/7.ccls. or 438/16.ccls. | USPAT | 2004/09/08 16:43 |
| 10 | 5 | immersion adj lithography | USPAT | 2004/09/08 17:38 |
| 11 | 0 | ((356/\$).CCLS.) and (immersion adj lithography) | USPAT | 2004/09/08 17:00 |
| 12 | 77 | ((356/\$).CCLS.) and (lithography with (water or liquid or vapor or medium or solution or bath)) | USPAT | 2004/09/08 17:01 |
| 13 | 23 | immersion adj lithography | US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/08 17:38 |